乞掲示

理化学研究所原子核セミナー　*2005. 7. 25*

講師 ： **Dr. Zheng Li**

(Brookhaven National Laboratory)

題目 ： Si Detector Development and Radiation Hardness for Nuclear and High Energy Physics Experiments at BNL and Around the World

∗ The seminar will be given in *English.*

日時 ： 2005 年　7 月　25 日 (Mon.)　14:00 –

場所 ： RIKEN Main Bldg. 2F Seminar Room

Abstract

Various prototype Si detectors with traditional configurations, including micro strip detectors, pad and pixel detectors, Si drift detectors have been developed and processed at BNL's Si Detector Development and Processing Lab (SDDPL) over the past 10 years for nuclear and high energy experiments at BNL and other institutes around the world. Specifics of these traditional detectors will be given and discussed. Novel Si detectors, including the 2d Si stripixel detectors, have been developed at BNL in the last few years. The standard Si stipixel detectors are all planar, single-sided process, 2d-position sensitive due to the charge sharing between the X and Y cells. New Si stripixel detector schemes with automatic charge distribution (not sharing) between X and Y cells will be given. New AC coupling schemes on these stripixel detectors will be proposed. Radiation induced damage and degradation of detectors will be discussed. New developments in the radiation hardness of Si detectors will be reviewed.

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原子核セミナーについてのお問い合わせ

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